



UTN6266

Preliminary

Power MOSFET

30A, 60V N-CHANNEL TRENCH MOSFET

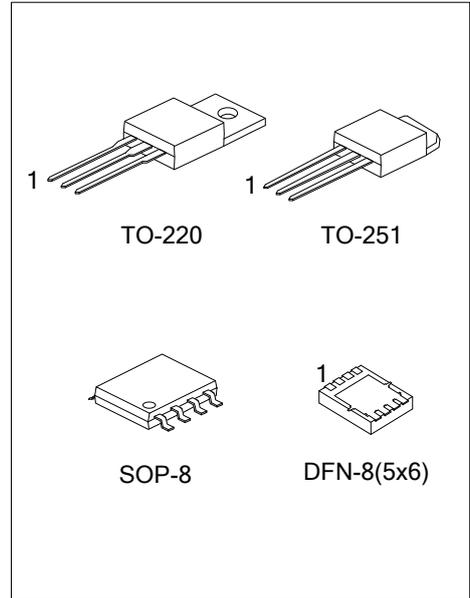
■ DESCRIPTION

The UTC **UTN6266** is an N-Channel trench mosfet, it uses UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed and low gate charge.

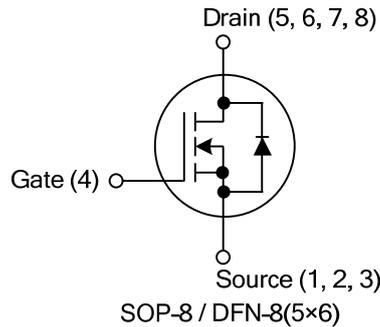
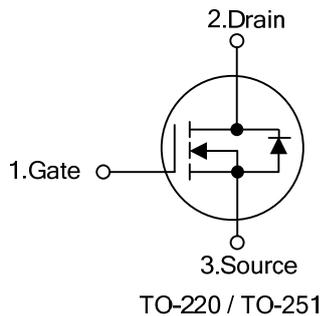
The UTC **UTN6266** is suitable for Synchronous Rectification in DC/DC and AC/DC Converters and industrial and Motor Drive applications.

■ FEATURES

- * $R_{DS(ON)} < 15m\Omega$ @ $V_{GS}=10V, I_D=20A$
- * $R_{DS(ON)} < 19m\Omega$ @ $V_{GS}=4.5V, I_D=18A$
- * Low gate charge
- * Low $R_{DS(ON)}$
- * High switching speed



■ SYMBOL



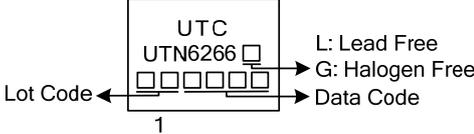
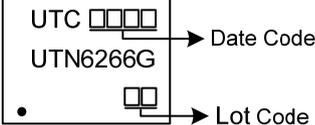
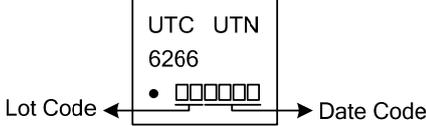
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UTN6266L-TA3-R	UTN6266G-TA3-R	TO-220	G	D	S	-	-	-	-	-	Tape Reel
UTN6266L-TM3-R	UTN6266G-TM3-R	TO-251	G	D	S	-	-	-	-	-	Tube
-	UTN6266G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel
-	UTN6266G-K08-5060-R	DFN-8(5x6)	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UTN6266L-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TM3: TO-251, S08: SOP-8, K08-5060: DFN-8(5x6)</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING

Package	Marking
TO-220 / TO-251	
SOP-8	
DFN-8(5x6)	

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	30	A
	Pulsed	I_{DM}	90	A
Avalanche Current (Note 3)		I_{AS}	20	A
Avalanche Energy (Note 2, 3)		E_{AS}	280	mJ
Power Dissipation	TO-220	P_D	2	W
	TO-251		1.2	W
	SOP-8		1.5	W
	DFN-8(5×6)		1.92	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Single pulse width by junction temperature $T_{J(max)}=150^\circ\text{C}$.

3. $L = 1.4\text{mH}$, $I_{AS} = 20\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	θ_{JA}	200	$^\circ\text{C/W}$
	TO-251		60	$^\circ\text{C/W}$
	SOP-8		85	$^\circ\text{C/W}$
	DFN-8(5×6)		65	$^\circ\text{C/W}$
Junction-to-Case	TO-220	θ_{JC}	4.38	$^\circ\text{C/W}$
	TO-251		2.6	$^\circ\text{C/W}$
	SOP-8		24	$^\circ\text{C/W}$
	DFN-8(5×6)		12	$^\circ\text{C/W}$

Notes: 1. The θ_{JA} is the sum of the thermal impedance from junction to case θ_{JC} and case to ambient.

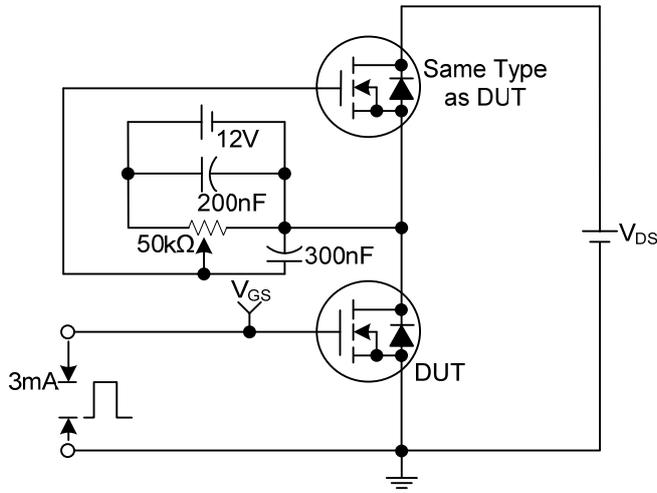
2. The value of θ_{JA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper.

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise noted)

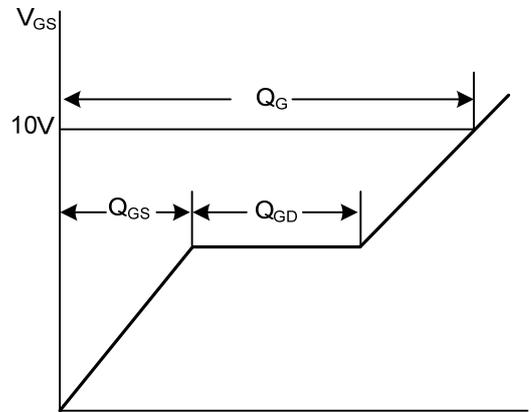
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$			5	μA
Gate-Body Leakage Current	Forward	I_{GSS}				
	Reverse					
		$V_{GS}=+20\text{V}$, $V_{DS}=0\text{V}$			+100	nA
		$V_{GS}=-20\text{V}$, $V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.5	2.0	2.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=20\text{A}$		12	15	m Ω
		$V_{GS}=10\text{V}$, $I_D=20\text{A}$, $T_J=125^\circ\text{C}$		20.5	25	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=18\text{A}$		15	19	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=30\text{V}$, $f=1.0\text{MHz}$		390		pF
Output Capacitance	C_{OSS}			190		pF
Reverse Transfer Capacitance	C_{RSS}			170		pF
Gate Resistance	R_G	$f=1.0\text{MHz}$		1.1		Ω
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $I_D=20\text{A}$		6		nC
Gate to Source Charge	Q_{GS}			0.5		nC
Gate to Drain Charge	Q_{GD}			0.5		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $R_L=1.5\Omega$, $R_{GEN}=3\Omega$		60		ns
Rise Time	t_R			75		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			500		ns
Fall-Time	t_F			230		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				30	A
Drain-Source Diode Forward Voltage (Note2)	V_{SD}	$I_S=1\text{A}$, $V_{GS}=0\text{V}$	0.72	1		V

- Notes: 1. Pulse width limited by $T_{J(MAX)}$
 2. Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
 3. Surface Mounted on 1in^2 pad area.

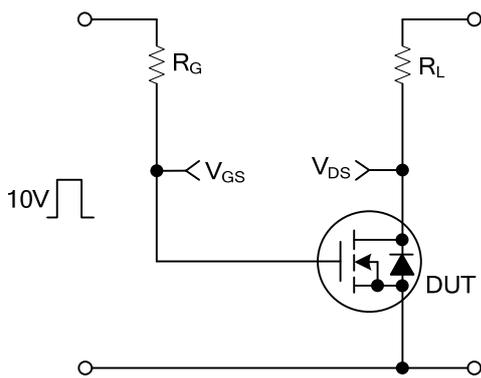
■ TEST CIRCUITS AND WAVEFORMS



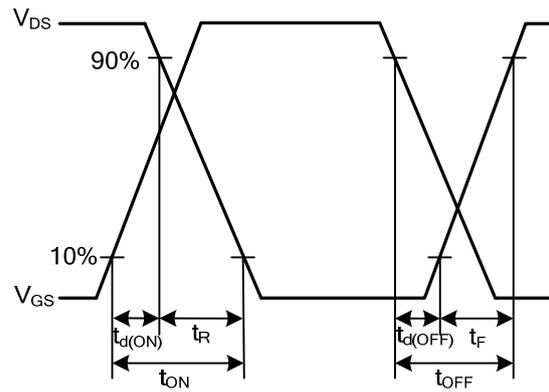
Gate Charge Test Circuit



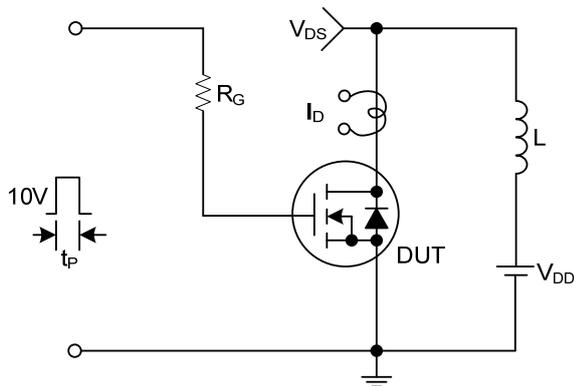
Gate Charge Waveforms



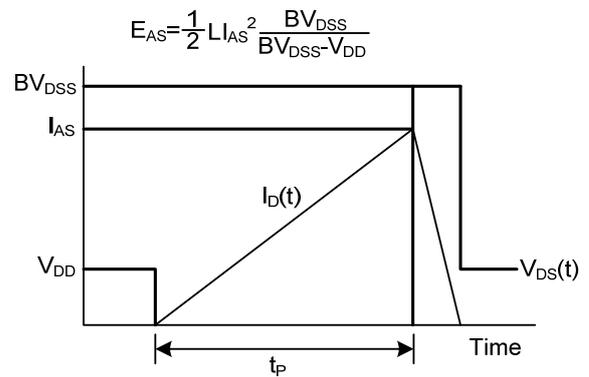
Resistive Switching Test Circuit



Resistive Switching Waveforms

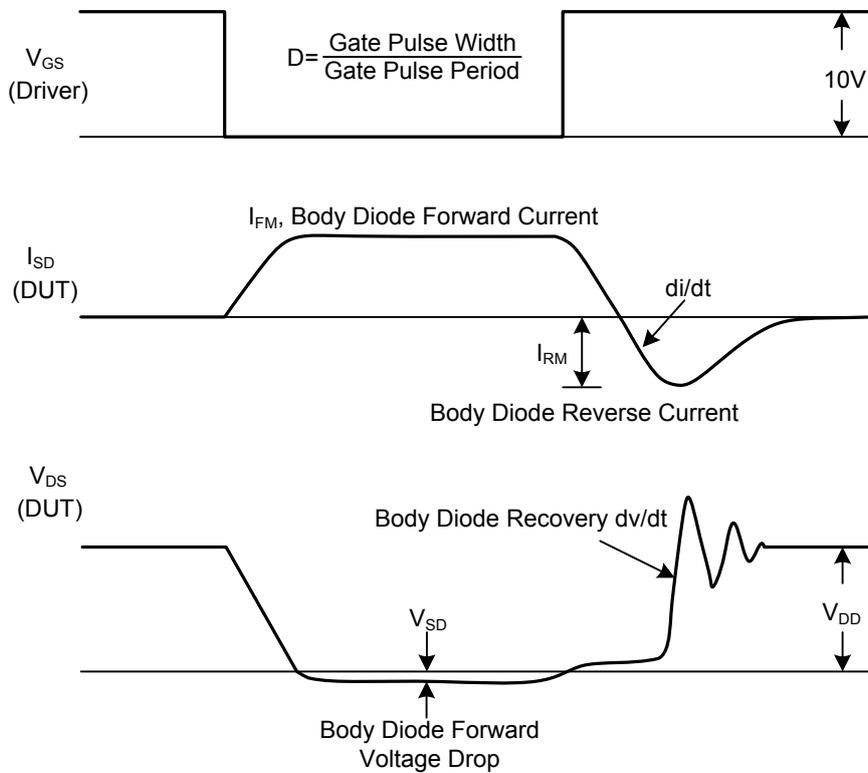
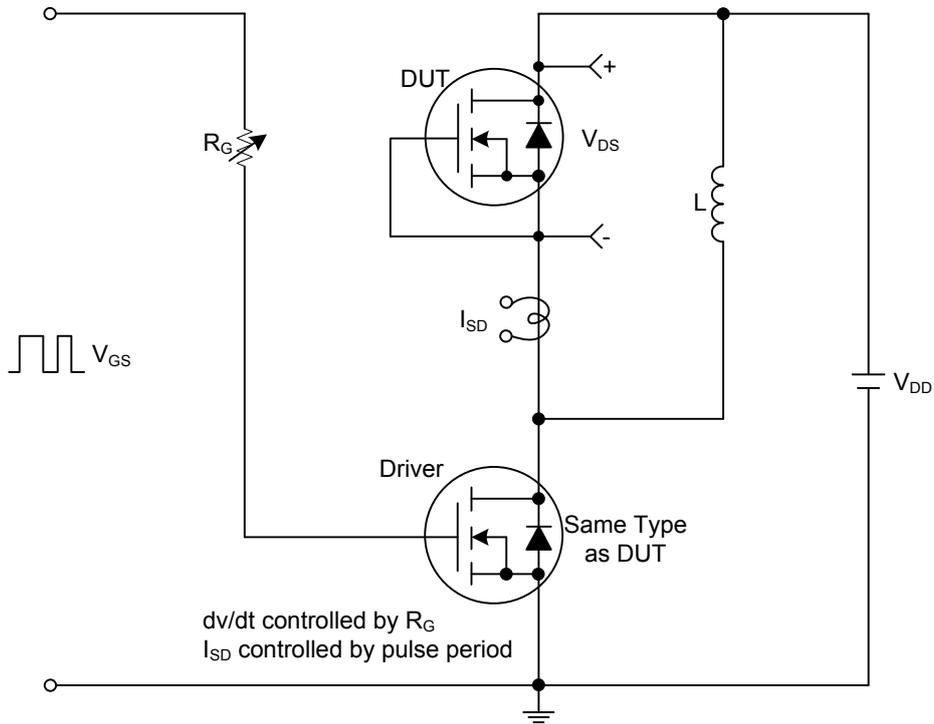


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)



Peak Diode Recovery dv/dt Test Circuit and Waveforms

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